Abstract of the Disclosure

A semiconductor device and a method for releasing stress exerted while fabricating the semiconductor device. The method for releasing the stress, includes forming a stack layer deposited on a semiconductor sequentially with a gate oxide layer, a poly-silicon layer, a tungsten layer, and a hard mask; selectively oxidizing, wherein only the poly-silicon layer of the stack layer is oxidized; heat treating for releasing stress exerted during the selective oxidation process; and forming a gate sealing nitride layer on the stack layer heat-treated.